

SANYO

No.3162

2SK1233

N-Channel GaAs MES FET

**4GHz-Band Local Oscillator,
Amplifier Applications****Features**

- Casting mold package
- Suited for 4GHz-band local oscillator
- Adoption of high reliable protection film

Absolute Maximum Ratings at Ta=25°C

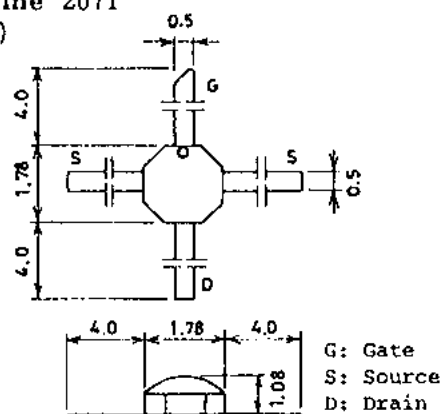
Drain to Source Voltage	V_{DS}	6	V
Gate to Source Voltage	V_{GS}	-5	V
Drain Current	I_D	100	mA
Allowable Power Dissipation	P_D	300	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-65 to +150	°C

Electrical Characteristics at Ta=25°C

		min	typ	max	unit
Gate to Drain Breakdown Voltage	$V_{(BR)GDS}$	$I_G = -10\mu A, V_{DS} = 0V$	-5		V
Gate Cutoff Current	I_{GSS}	$V_{GS} = -3V, V_{DS} = 0V$		-10	μA
Drain Current	I_{DSS}	$V_{DS} = 3V, V_{GS} = 0V$	20	60	mA
Gate to Source Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 3V, I_D = 100\mu A$	-0.5	-5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = 3V, I_D = 10mA$	20	40	mS
Noise Figure	NF	$V_{DS} = 3V, I_D = 10mA, f = 4GHz$	1.2	1.5	dB
		$f = 8GHz$	2		dB
Associated Gain	G_a	$V_{DS} = 3V, I_D = 10mA, f = 4GHz$	8.5	11	dB
		$f = 8GHz$	8		dB
Maximum Stabilized Power Gain	MSG	$V_{DS} = 3V, I_D = 30mA, f = 4GHz$	12		dB
Maximum Oscillation Frequency	f_{max}	$V_{DS} = 3V, I_D = 30mA$	40		GHz

The application circuit diagrams and circuit constants herein are included as an example and provide no guarantee for designing equipment to be mass-produced.

The information herein is believed to be accurate and reliable. However, no responsibility is assumed by SANYO for its use, nor for any infringements of patents or other rights of third parties which may result from its use.

Case Outline 2071
(unit: mm)

Specifications and information herein are subject to change without notice.

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